The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

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Parameter	Value		Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	700		V
$I_{D,\ pulse}$	114		A
$R_{DS(ON),\ max}$ @ V_{GS}=10V	99		m
Q_g	42.6		nC

Absolute Maximum Ratings at T_j=25 unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	38	A
Continuous drain current[1], T_C=100 °C		24	
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	114	A
Continuous diode forward current[1], T_C=25 °C	I_S	38	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	114	A
Power dissipation[3] ,T_C=25 °C	P_D	278	W
Single pulsed avalanche energy[5]	E_{AS}	1200	mJ
MOSFET dv/dt ruggedness, V_{DS}	dv/dt	100	V/ns
Reverse diode dv/dt, V_{DS} SD D	dv/dt	50	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R	0.45	°C/W
Thermal resistance, junction-ambient[4]	R	62	°C/W

Electrical Characteristics at T_j=25 unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	V_{GS}=0 V, I_D=1 mA
		700	770			V_{GS}=0 V, I_D=1 mA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	3.5		4.5	V	V_{DS}=V_{GS}, I_D=1 mA
Drain-source on-state resistance	$R_{DS(ON)}$		0.088	0.099		V_{GS}=10 V, I_D=19 A
			0.23			V_{GS}=10 V, I_D=19 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			10	A	V_{DS}=650 V, V_{GS}=0 V

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		3073		pF	V_{GS}=0 V, V_{DS}=50 V, MHz
Output capacitance	C_{oss}		448.8		pF	
Reverse transfer capacitance	C_{rss}		7.3		pF	
Turn-on delay time	$t_{d(on)}$		36.6		ns	V_{GS}=10 V, V_{DS}=400 V, R_G I_D=20 A
Rise time	t_r		57.4		ns	
Turn-off delay time	$t_{d(off)}$		39.6		ns	
Fall time	t_f		3.6		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		42.5		nC	V_{GS}=10 V, V_{DS}=400 V, I_D=20 A
Gate-source charge	Q_{gs}		14		nC	
Gate-drain charge	Q_{gd}		12.2		nC	
Gate plateau voltage	$V_{plateau}$		6.0		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	I_S=38 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		162		ns	I_S=20 A, di/dt=100
Reverse recovery charge	Q_{rr}		1.12		uC	
Peak reverse recovery current	I_{rrm}		13		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of R is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100 V, V_{GS}=10 V, L=80 mH, starting T_j=25 °C.

Figure 7. Forward characteristic of body diode

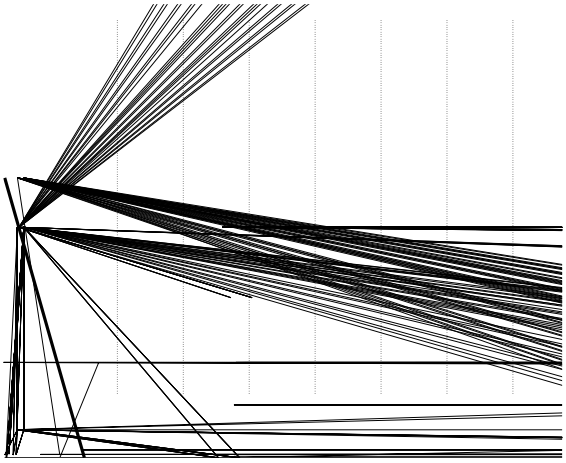


Figure 8. Drain-source on-state resistance

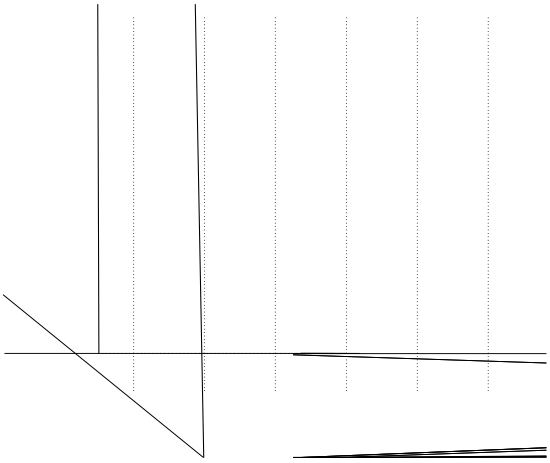
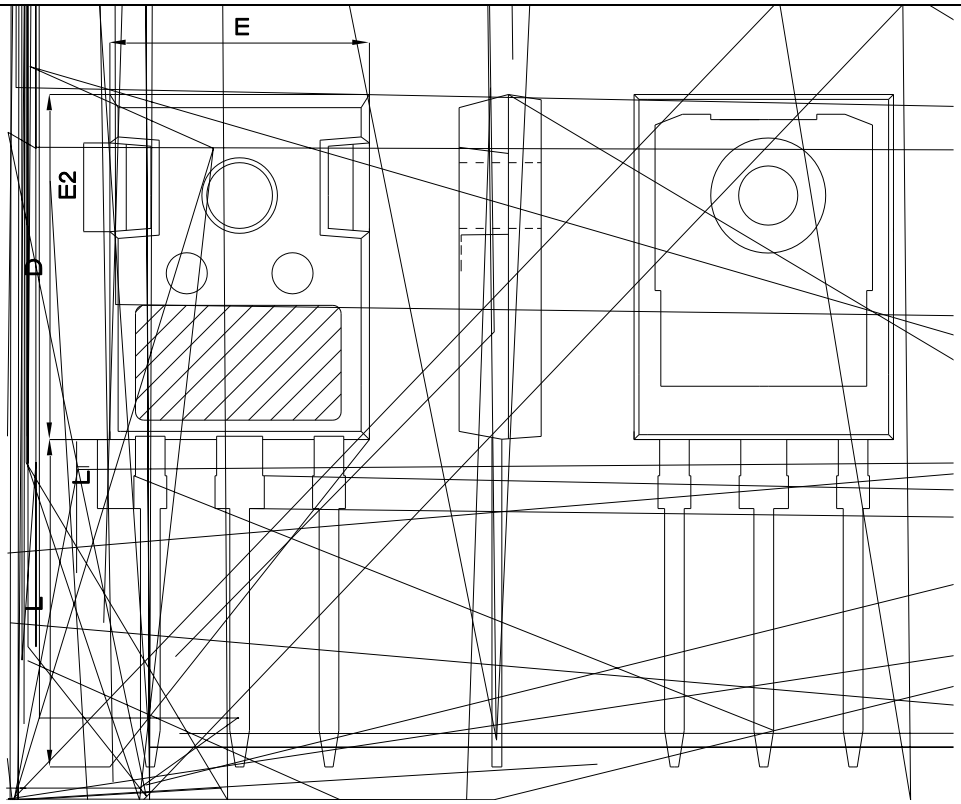


Figure 9. Drain current

Figure 10. Safe operation area T_C=25 °C

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
	3.40	3.60	3.80
	-	-	7.30
S	6.15BSC		

Version1: TO247-C package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-C	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R099HZF	TO247	yes	yes	yes